



Exploring glass surface with high-resolution XPS and LEIS:

Examples of Fundamental Studies and Applications

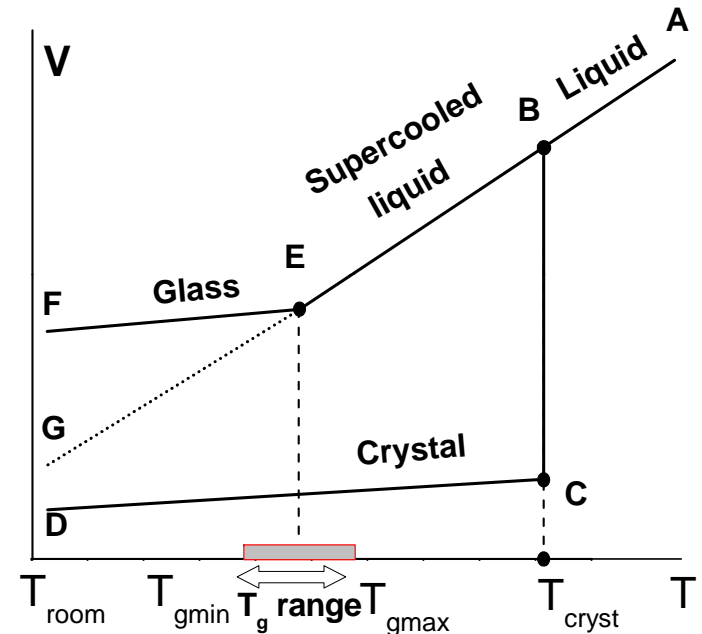
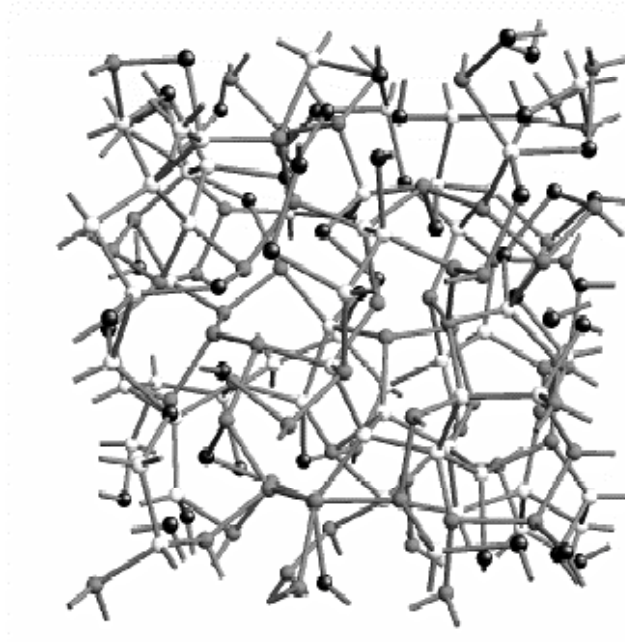
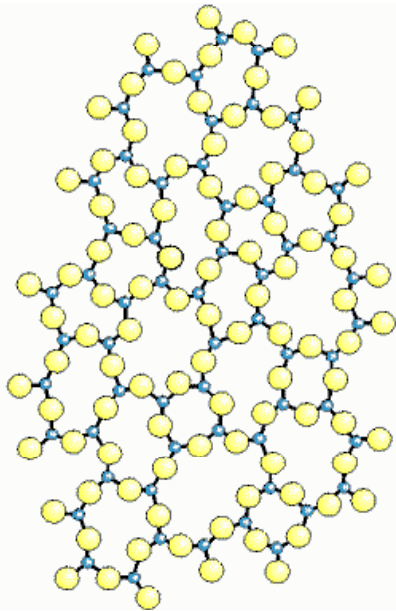
Andriy Kovalskiy

*Materials Science & Engineering Department
Lehigh University, PA*

Co-authors: *Himanshu Jain, Bruce Koel, Alfred Miller, Miroslav Vlcek,
Roman Golovchak, Keisha Antoine, Maria Mitkova*

“The surface was invented by the devil”
Wolfgang Pauli

Glass structure – lack of translational symmetry



High-resolution XPS:

one of the fundamental structural methods in glass science

Other methods:

Raman/FTIR spectroscopy, EXAFS, NMR

State of the art high resolution XPS vs “normal” XPS

G.J. Adriaenssens et al. / Journal of Non-Crystalline Solids 266-269 (2000) 898-903

901

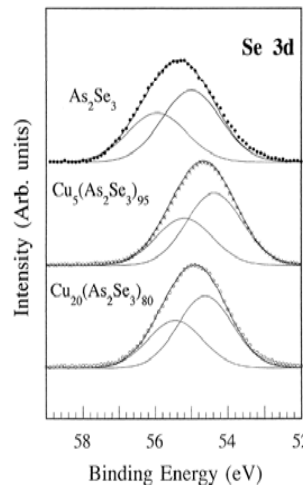
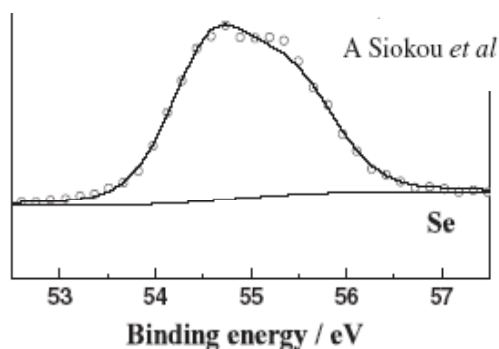


Fig. 3. XPS binding energy spectrum of the Se 3d core electrons in the indicated compounds, together with a decomposition (full lines) of the spectra into their $3d_{1/2}$ and $3d_{3/2}$ components.

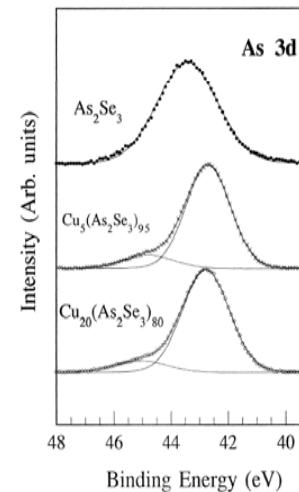
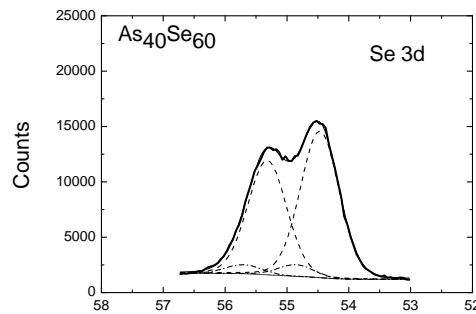
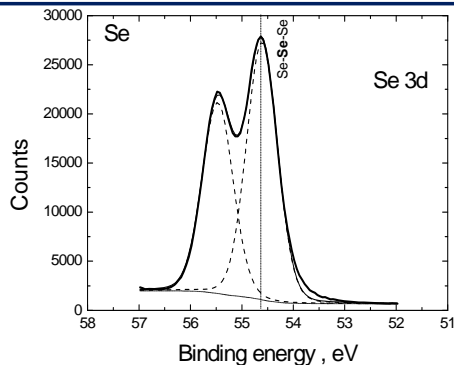
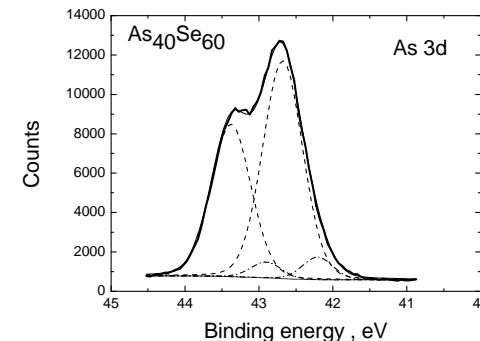


Fig. 4. XPS binding energies of the As 3d core electrons for the indicated selenide compositions, also showing a decomposition (full lines) which includes the small arsenic oxide contribution that is observed in the Cu-containing samples.



PHYSICAL REVIEW B 76, 125208 (2007)



Structure of Se-rich As-Se glasses by high-resolution x-ray photoelectron spectroscopy

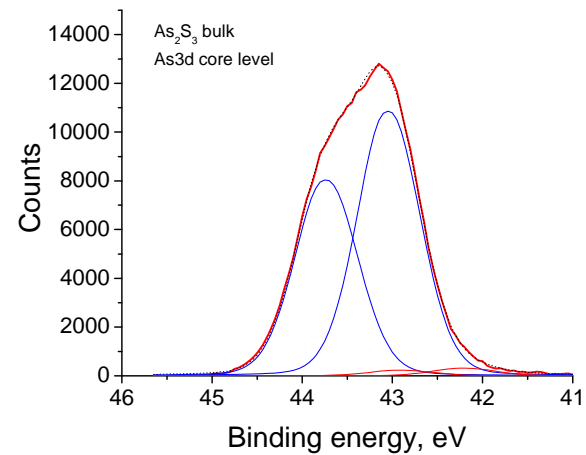
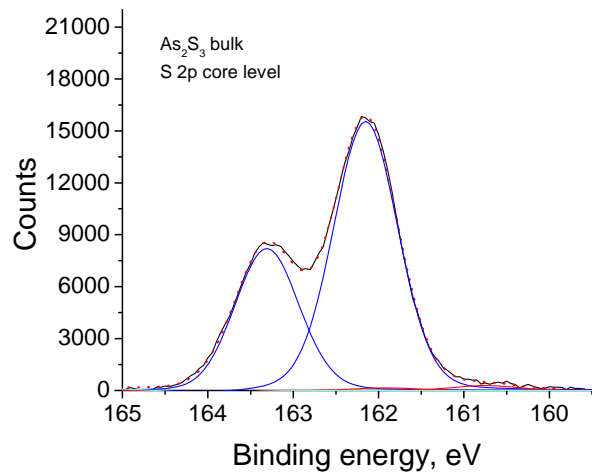
R. Golovchak

Lviv Scientific Research Institute of Materials of SRC "Carat," 202 Stryjska street, Lviv, UA-79031, Ukraine

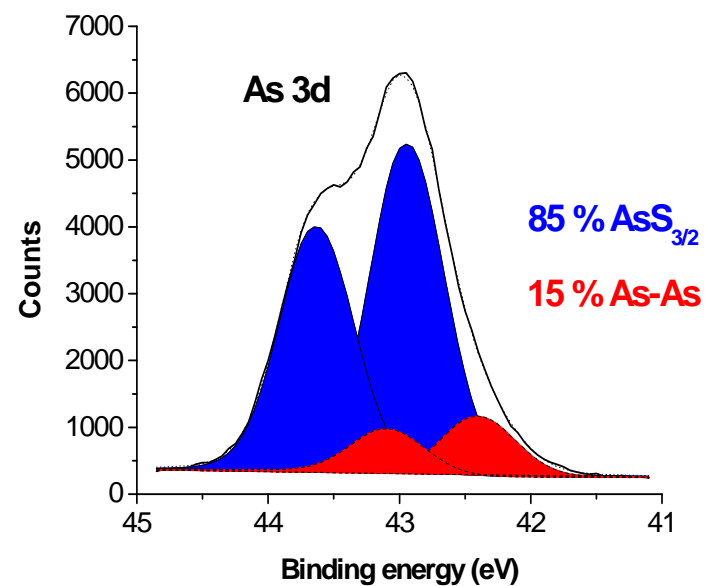
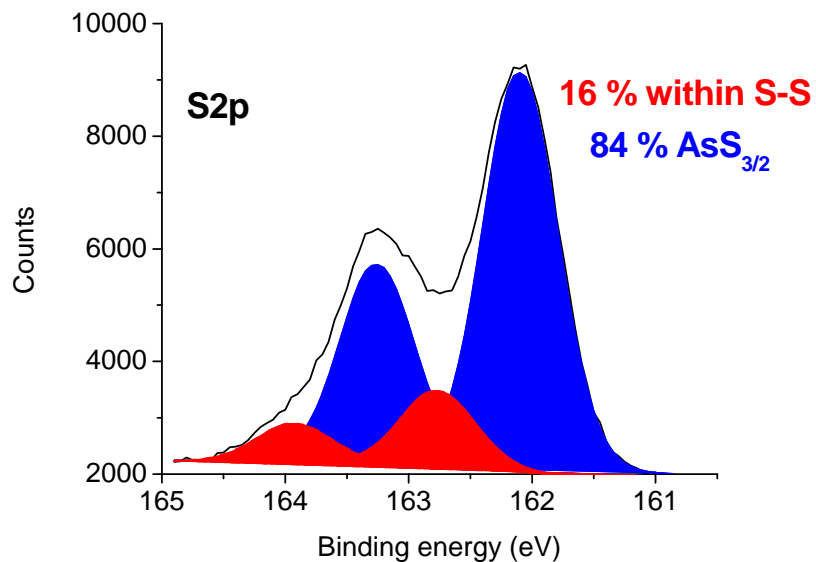
A. Kovalskiy, A. C. Miller, and H. Jain*

Department of Materials Science and Engineering, Lehigh University,
5 East Packer Avenue, Bethlehem, Pennsylvania 18015-3195, USA

Structure of fresh cut of glass vs freshly deposited thin film



Bulk As₂S₃



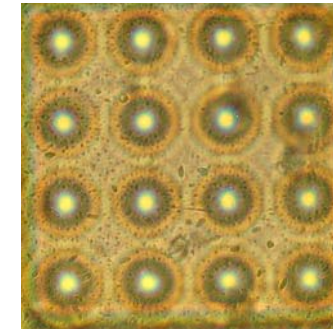
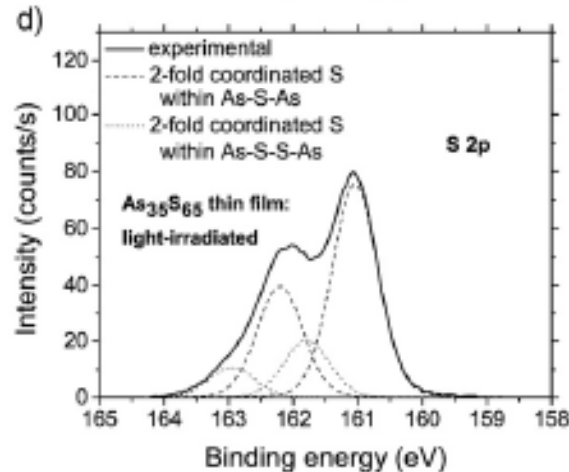
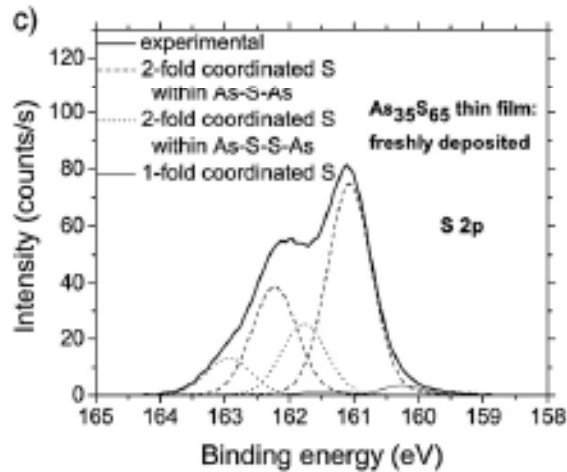
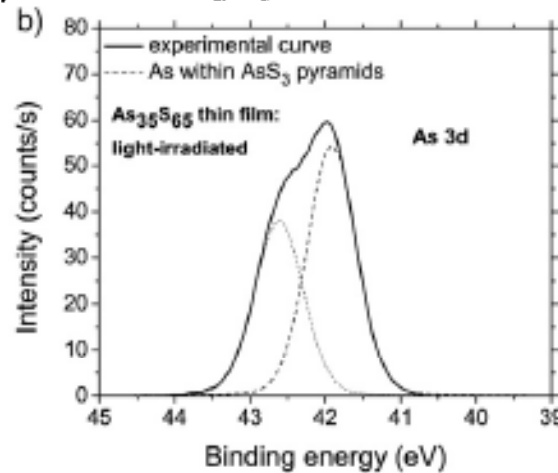
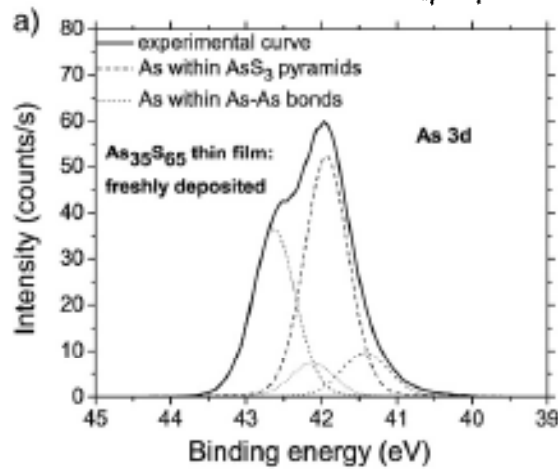
Freshly deposited As₂S₃ film

Thin films: photostructural transformations by XPS



Comparative study of electron- and photo-induced structural transformations on the surface of $As_{35}S_{65}$ amorphous thin films

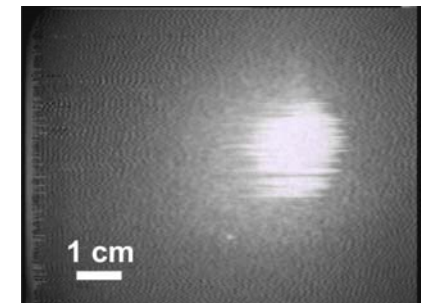
A. Kovalskiy ^{a,*}, J.R. Neilson ^a, A.C. Miller ^a, F.C. Miller ^b, M. Vlcek ^c, H. Jain ^a



Array of Fresnel lenses with focal point $\sim 300 \mu m$



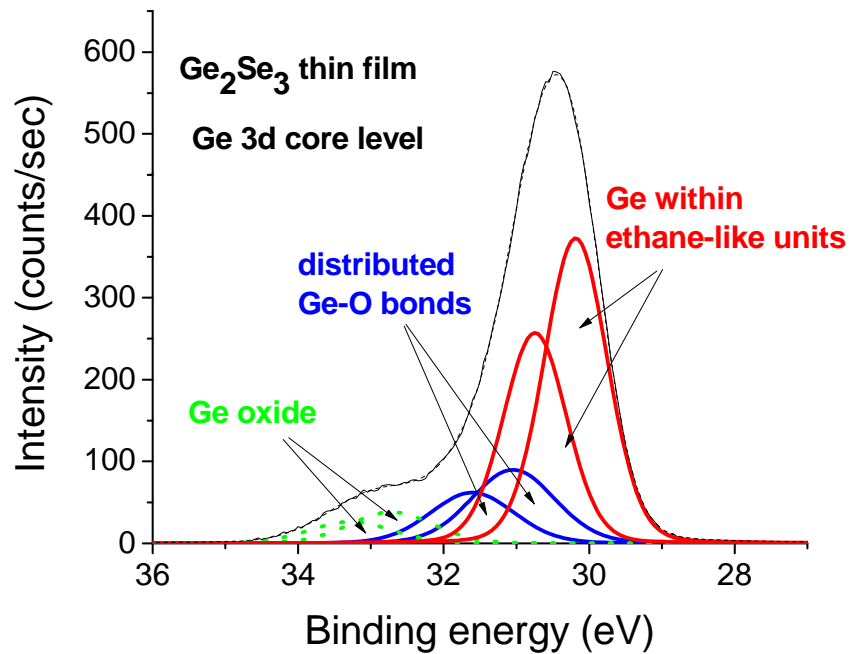
Fresnel lens with focal point $\sim 5.38 mm$



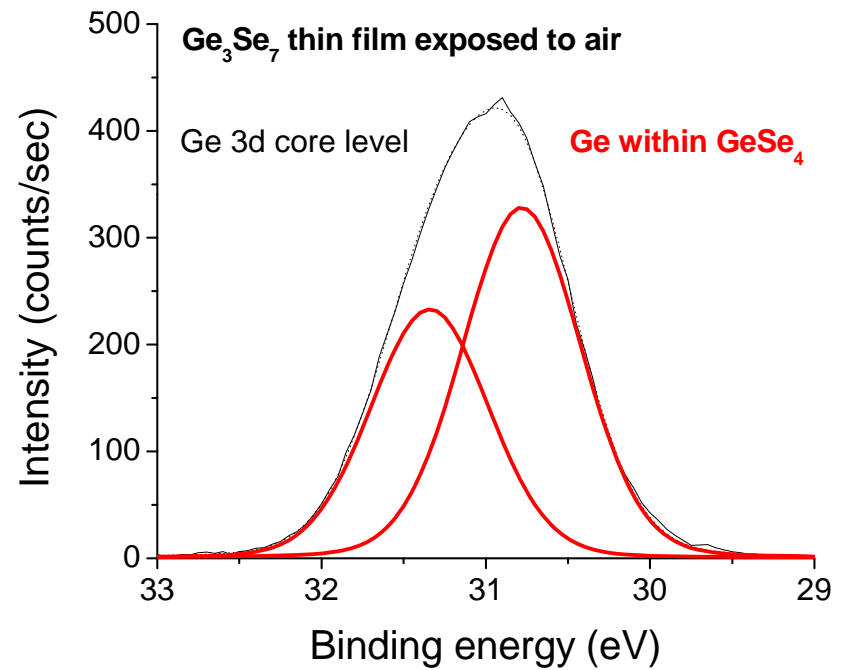
IR laser beam ($1.55 \mu m$) focused by Fresnel lens on Si substrate

Photooxidation on the surface of ChG

Oxidation in air strongly depends on Ge content



Strong oxidation in air



No oxidation in air

E-beam Patterning of Chalcogenide Glasses



Available online at www.sciencedirect.com



Journal of Non-Crystalline Solids 353 (2007) 1427–1430

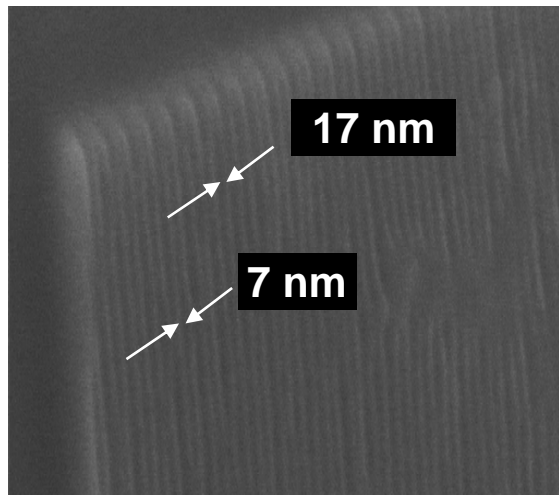
JOURNAL OF
NON-CRYSTALLINE SOLIDS

www.elsevier.com/locate/jnocrsol

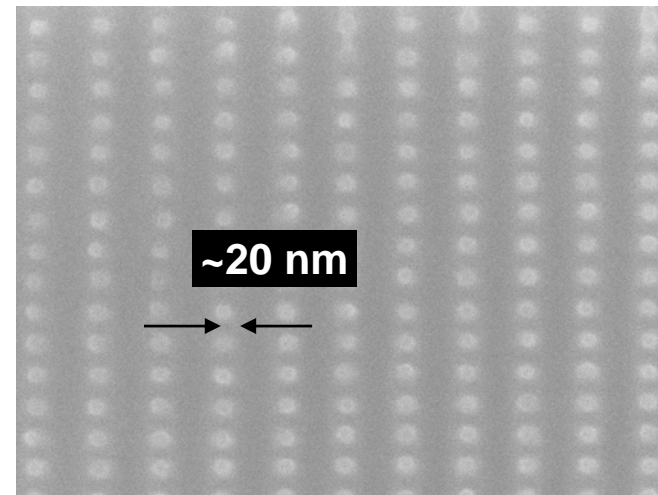
Fabrication of nano-gratings in arsenic sulphide films

J.R. Neilson ^a, A. Kovalskiy ^a, M. Vlček ^b, H. Jain ^{a,*}, F. Miller ^c

What is the resolution limit for ChG?



Finest structural features on glasses



Direct observation of separate e-beam spots

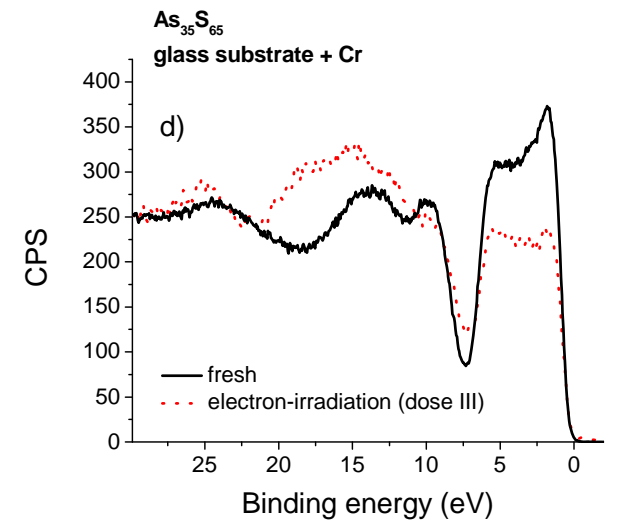
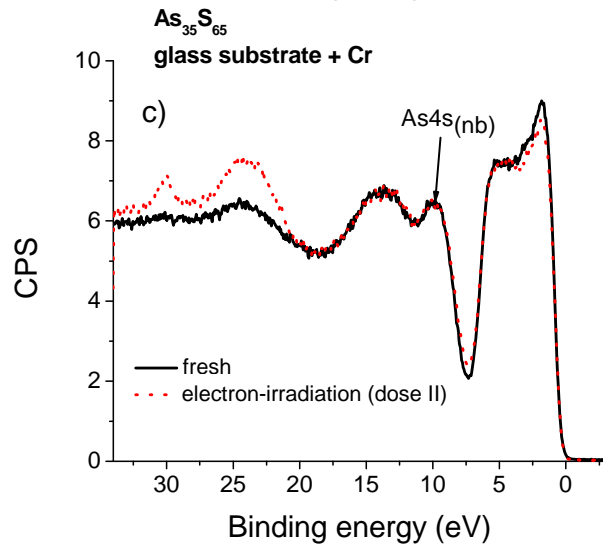
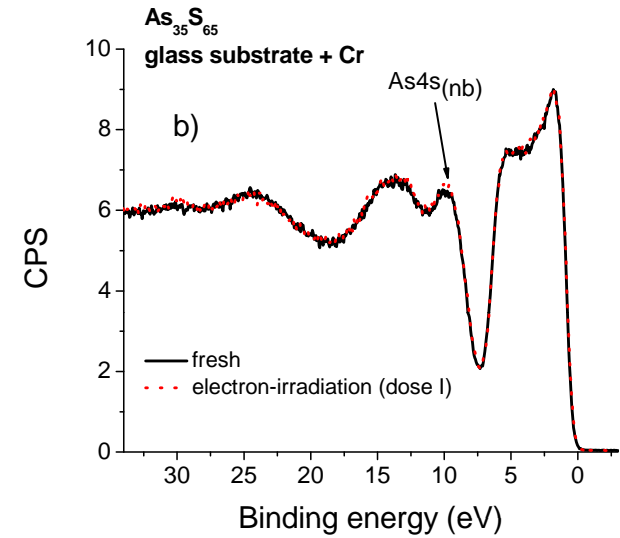
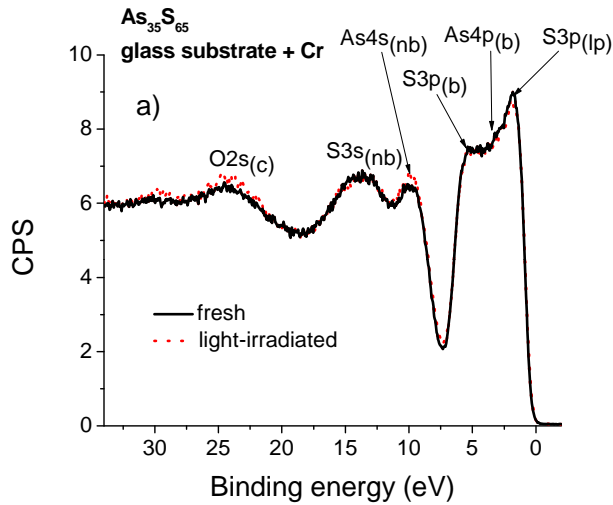
Wet Etching in Amine Solution

Structural Origin of E-beam Patterning of Chalcogenide Glasses



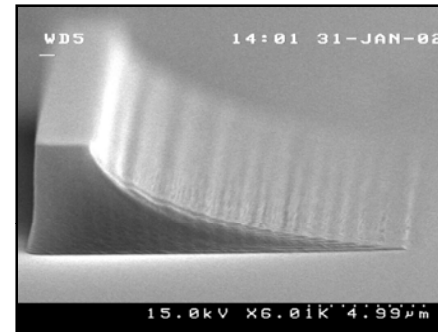
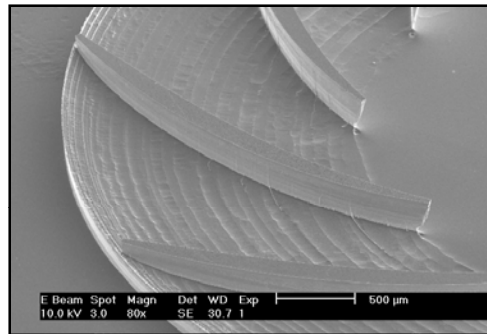
Comparative study of electron- and photo-induced structural transformations on the surface of $As_{35}S_{65}$ amorphous thin films

A. Kovalskiy ^{a,*}, J.R. Neilson ^a, A.C. Miller ^a, F.C. Miller ^b, M. Vlcek ^c, H. Jain ^a

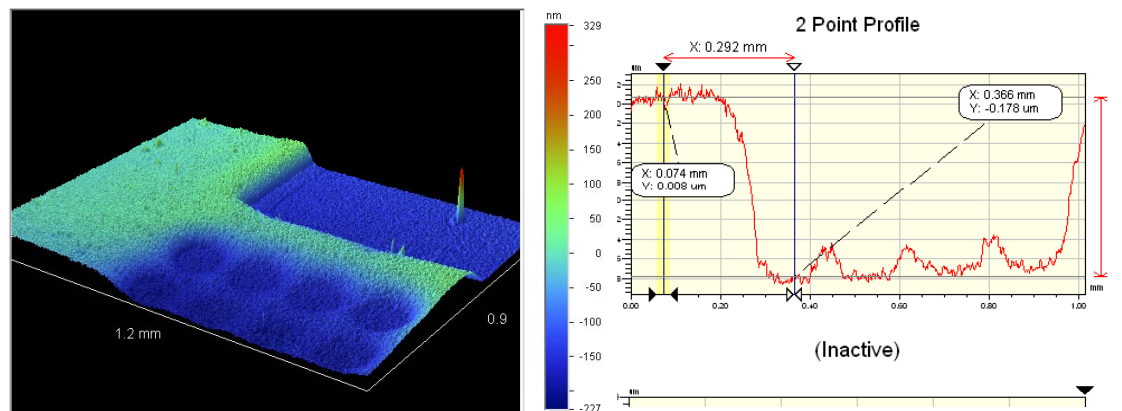


Gray Scale Lithography based on Ag Photodiffusion in Chalcogenide Glass Thin Films

Motivation: 3-D profiles in photoresist film for development of microturbine compressor with smooth blades



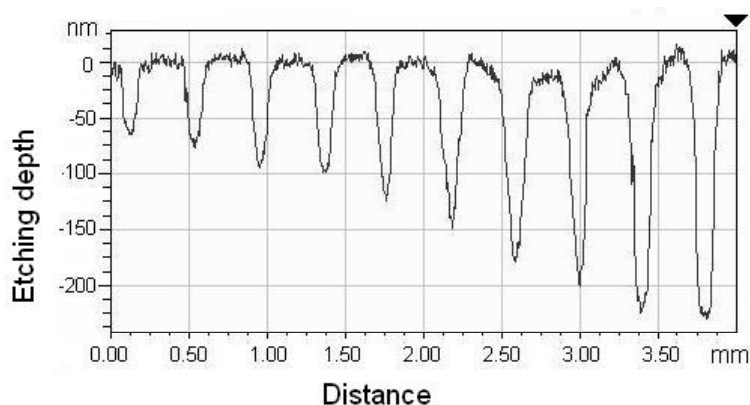
Example of complex shape structure on the surface— negative dry etching



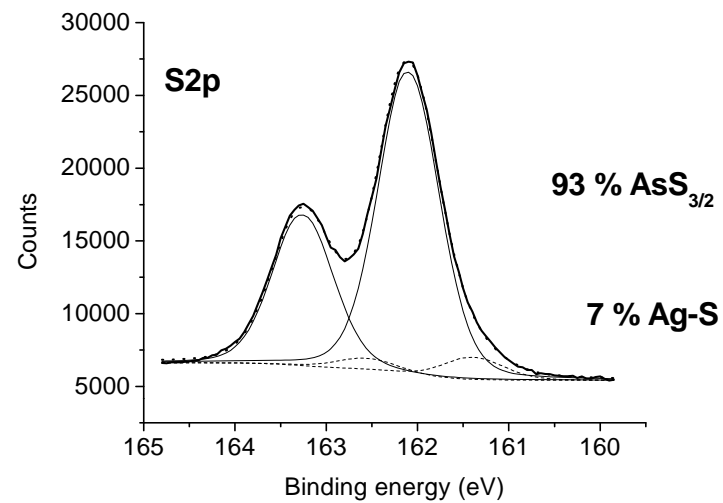
Si substrate to ChG thickness transfer ratio of > 10 is achieved

Gray Scale Lithography based on Ag Photodissolution into Chalcogenide Glass Thin Films

- Ag dissolves into As-S glass in step like mode
- depth of dissolution - function of exposure dose

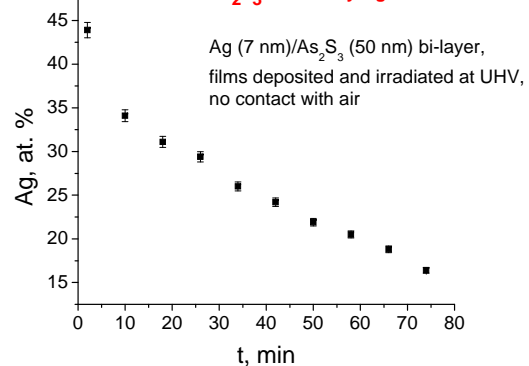


Profilogram demonstrating the change of etching depth with gradual variation of transparency of mask fragments.



Control of composition

Kinetics of X-ray-induced silver dissolution from the surface of a-As₂S₃ thin film by high-resolution XPS



Kinetics of X-ray-induced Ag dissolution



Available online at www.sciencedirect.com



Journal of Physics and Chemistry of Solids 68 (2007) 920–925

JOURNAL OF
PHYSICS AND CHEMISTRY
OF SOLIDS

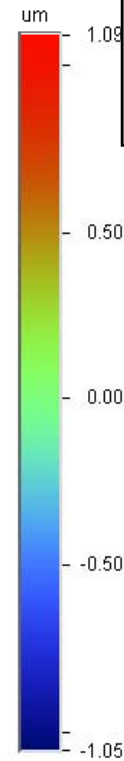
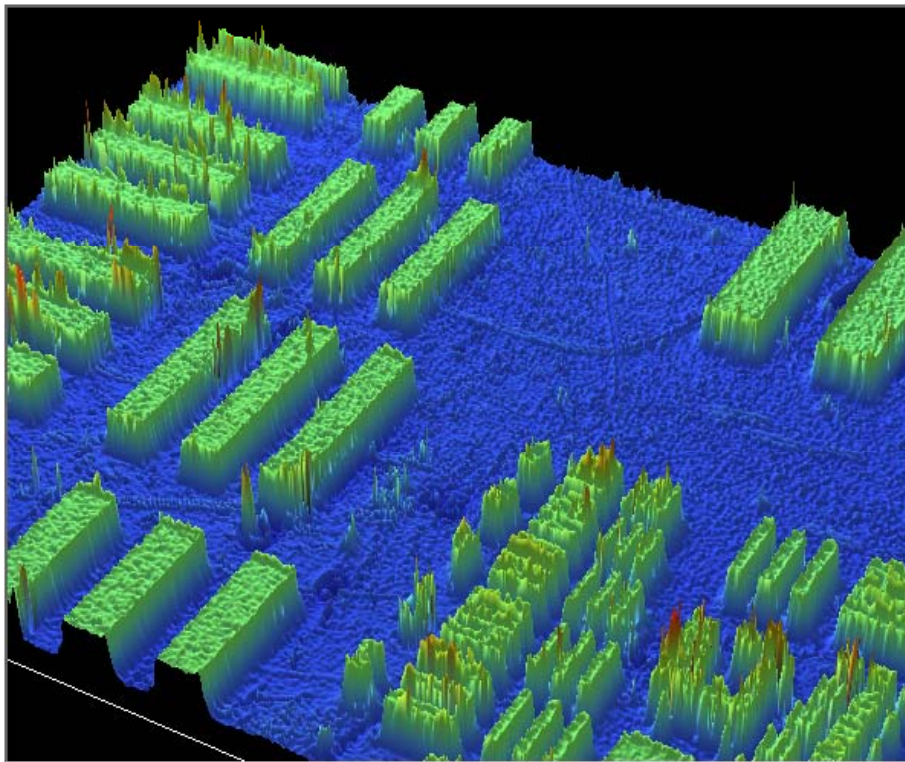
www.elsevier.com/locate/jpcs

On the mechanism of gray scale patterning of Ag-containing As₂S₃ thin films

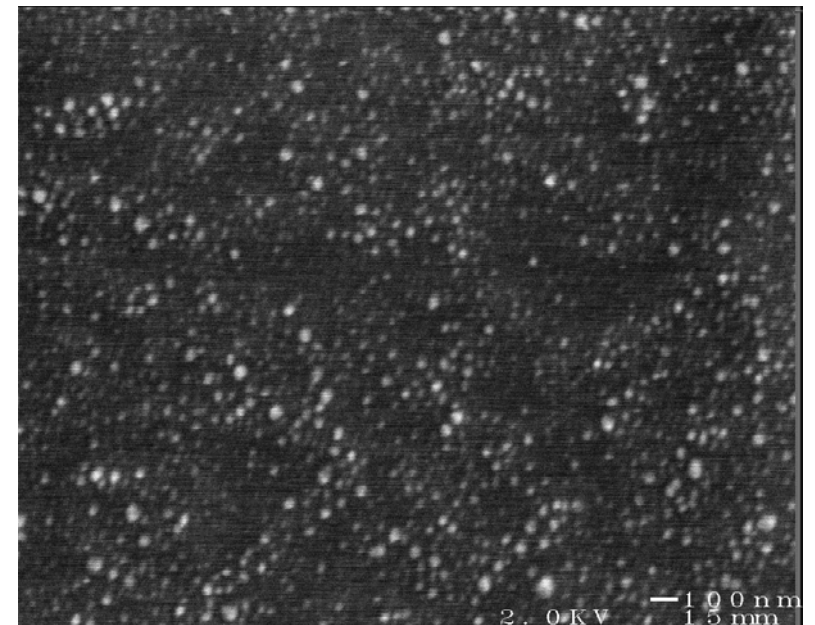
A. Kovalskiy^{a,*}, H. Jain^a, J. Neilson^a, M. Vlcek^b, C.M. Waits^c, W. Churaman^c, M. Dubey^c

Ag Photodiffusion into As_2S_3

Influence of surface oxidation?



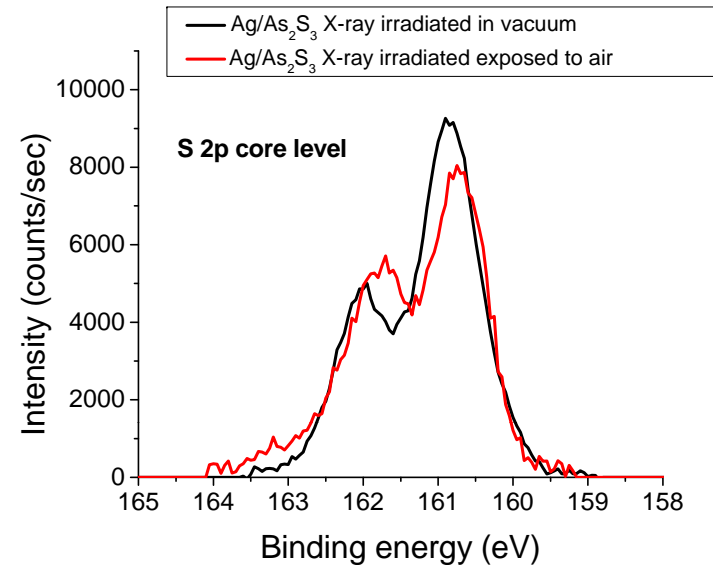
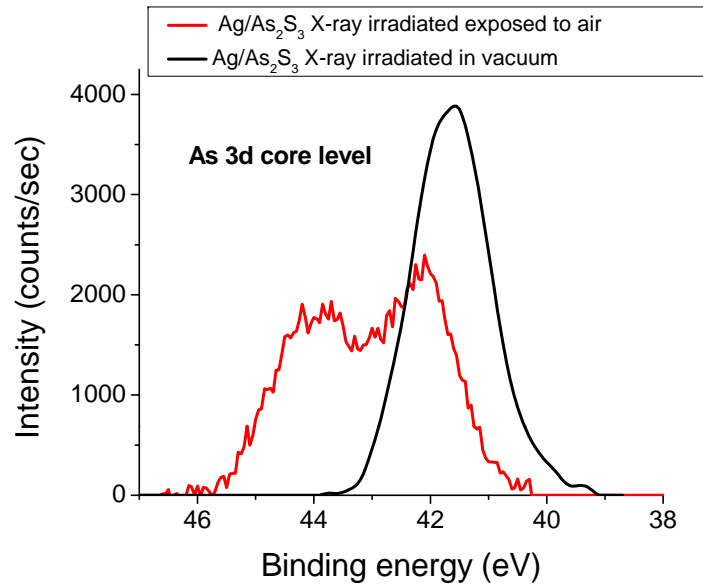
**ChG Surface after Photodiffusion
and Treatment in HNO_3 solution**



Spikes are due to: oxide clusters which etch differently.

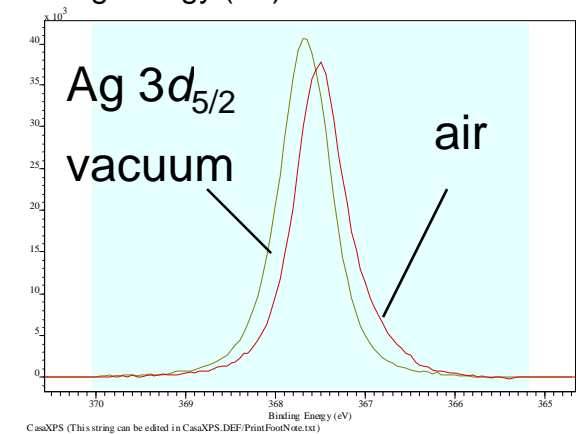
Ag Photodiffusion into ChG

Compare final products



FINAL PRODUCTS of Ag diffusion in vacuum and air:

- S chemical environment is similar, except that formation of ternary is slowed down by arsenic oxidation
- As chemical environment differs drastically:
 - phase separation due to oxidation in air;
 - some clustering of As in vacuum
- Ag chemical environment slightly differs due to As



Strong Glasses for Solar Energy



Concentrated Solar Thermal (CST)

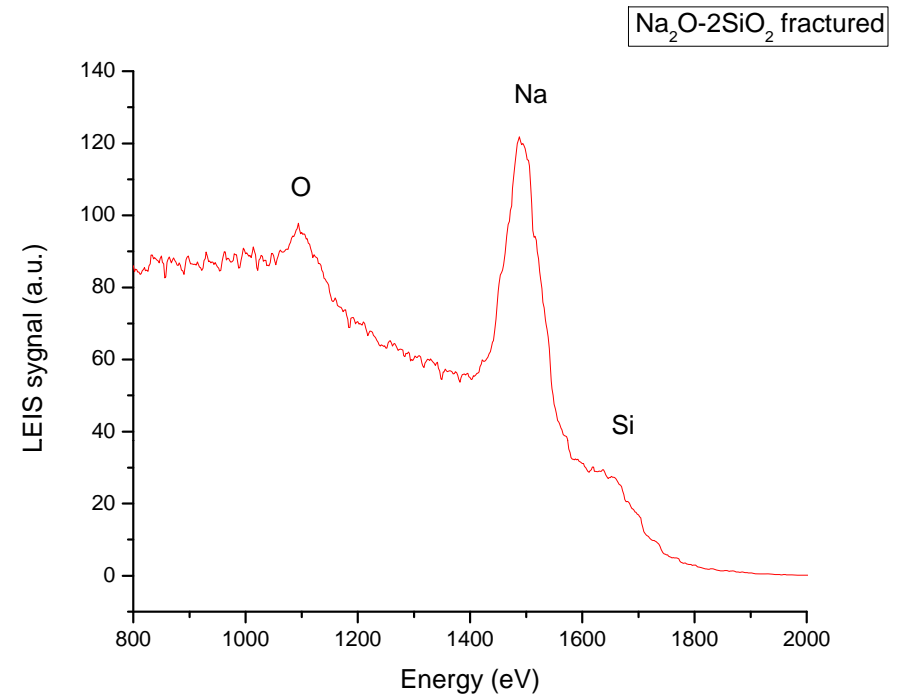
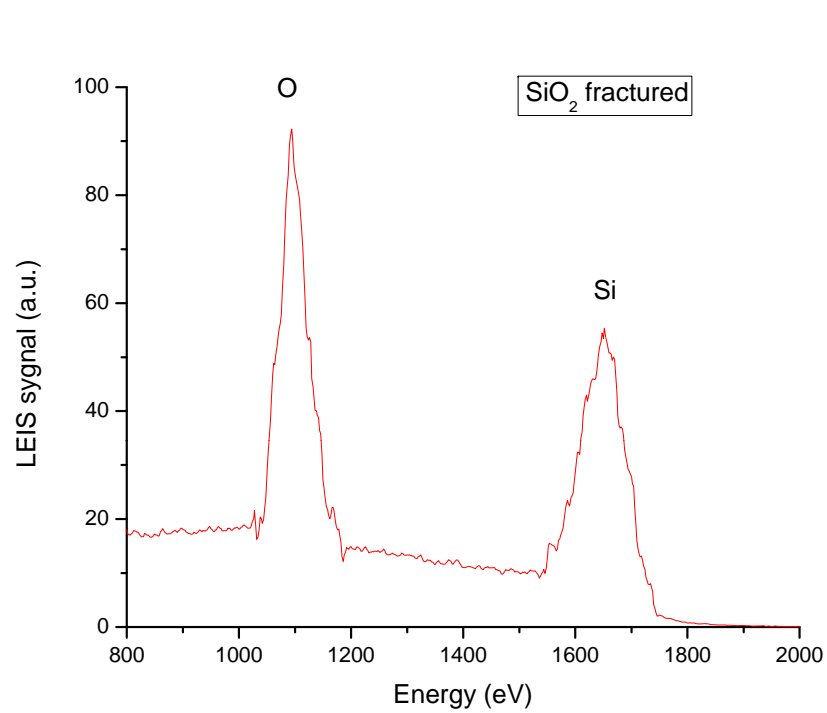
Photovoltaics: Increased strength to weight (thickness) to permit larger thin film module size

Methods: XPS, LEIS

Sodium silicate glasses – breaking path

Sample	Na	O	Si	Na/Si	BO/ NBO
Sodium disilicate, 90	21	55	24	0.875	2.2
Sodium disilicate, 25	19	59	22	0.86	2.3
Sodium disilicate heat treated, 90	20	55	25	0.80	2.3
Sodium disilicate heat treated, 25	21	54	25	0.84	2.2
Sodium trisilicate, 90	14	60	26	0.54	3.0
Sodium trisilicate, 25	24	56	20	1.20	2.4

Ion-TOF low energy ion scattering: first results



Low Energy Ion Scattering: Preliminary results

Sample	Si, at. %	O, at. %	Na, at. %	Na/Si
SiO ₂ fractured	35	65	-	-
Na ₂ O·2SiO ₂ fractured	8	17	75	9.4
Na ₂ O·2SiO ₂ treated 1 h at 620 °C, fractured	5	24	71	14.2
Na ₂ O·3SiO ₂ fractured	3	19	78	26.0

Conclusions

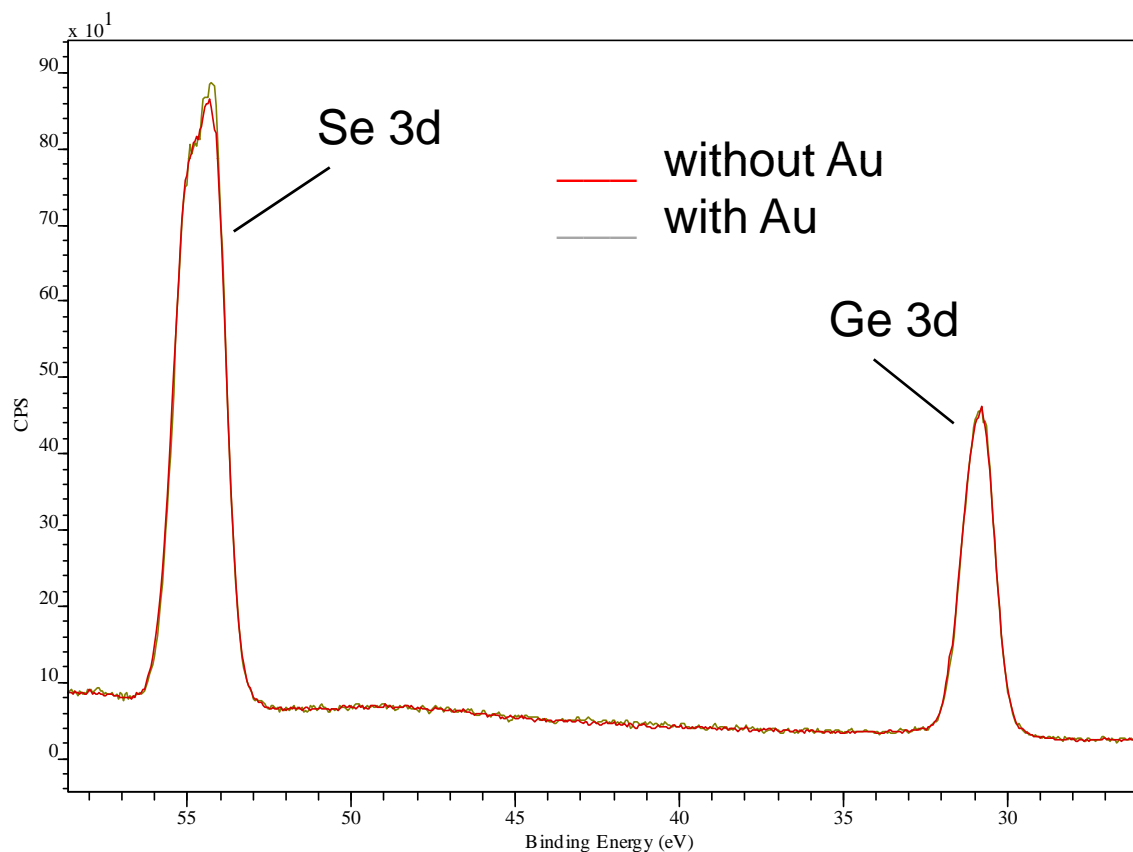


Binding Energy Referencing

Surface charge energy E_{ch} can be determined by electrically calibrating the instrument to a spectral feature.

C1s at 284.8 eV

Au4f_{7/2} at 84.0 eV



CasaXPS (This string can be edited in CasaXPS.DEF/PrintFootNote.txt)

Ge₃Se₇ – ideal referencing of Ge 3d to Au 4f_{7/2}